First Name:	
Last Name:	
Student Nun	hor

Student Number: Marks UNIVERSITY OF TORONTO Part A: FACULTY OF APPLIED SCIENCE AND ENGINEERING (/10)Final Exam – December 10, 2018 Part B: 1.(/20) First Year **2**.(/10) **APS110/164** – ENGINEERING CHEMISTRY AND MATERIALS SCIENCE 3.(/10) Exam Type: A **4**.(/10) Examiners – CQ Jia, SD Ramsay **5**.(/10) Duration: 150 minutes **6**.(/5) Permissible Calculators: Casio FX-991 or Sharp EL-520 • Rulers permitted **7**.(/10) • Answer all questions on this exam • All numerical responses must be expressed in the most appropriate units, including appropriate prefixes (ex. GPa TOTAL: rather than 10⁹ Pa), and be written with appropriate (/85) significant figures

Part A. Please enter the correct answer for the following questions on the computer answer form. (Each question is worth 1 mark)

- 1. Which of the following is the best explanation of the engineering stress?
 - a) The applied force divided by the initial cross-sectional area
 - b) The applied force divided by the instantaneous cross-sectional area
 - c) The applied force divided by the cross-sectional area within the necked region
 - d) None of the above
- 2. Regarding a standard tensile specimen, which of the following statements is true?
 - a) The gauge length is normally longer than the reduced section, but the reduced section is never longer than the gauge length
 - b) The gauge length is normally less than the reduced section, but the reduced section is never less than the gauge length
 - c) The reduced section and the gauge length are normally equal
 - d) None of the above
- 3. Which of the following would be expected to cause a change in the elastic modulus?
 - a) An increase in the impurity concentration in a metal
 - b) An increase in the dislocation density of a metal
 - c) A reduction in the grain size of a metal
 - d) An increase in crystallinity of a polymer
- 4. Which of the following is closest to the atomic scale?
 - a) 10⁻¹⁴ m
 - b) 10⁻⁶ m
 - c) 10⁻¹⁰ m
 - d) 10⁻²³ m
- 5. How many atoms are present within a single unit cell of the diamond cubic crystal structure?
 - a) 4
 - b) 5
 - c) 6
 - d) 8

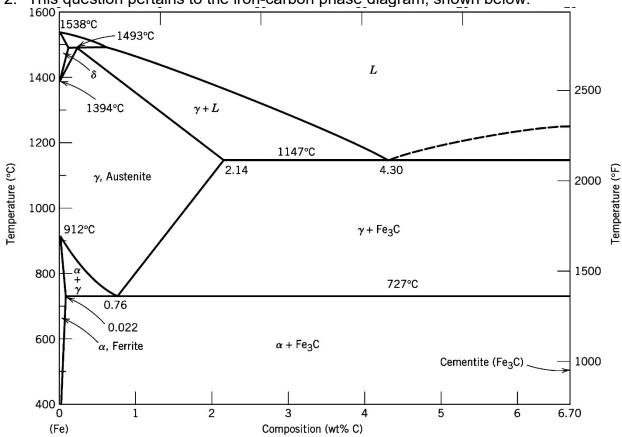
- 6. Which of the following is the most accurate description of the direction that atoms within the BCC crystal structure touch one another?
 - a) Along the face diagonals
 - b) Along the cube diagonals
 - c) Along the cube edges
 - d) None of the above
- 7. Which of the following best describes the stacking sequence of close-packed planes within the HCP crystal structure?
 - a) There are no close-packed planes in HCP
 - b) ABCABC
 - c) ABAB
 - d) None of the above
- 8. At higher temperatures stress relaxation would occur more rapidly.
 - a) False
 - b) True
- 9. A polymer that exhibits a very subtle (small) change in relaxation modulus around the glass-transition temperature would most likely have which of the following microstructures?
 - a) Fully amorphous
 - b) Cross-linked
 - c) Highly crystalline
 - d) None of the above
- 10.A reaction with a positive enthalpy change and a positive entropy change will be spontaneous under which of the following conditions?
 - a) At low temperature
 - b) At high temperature
 - c) At all temperatures
 - d) Never

Part B.

- 1. (20) Many ski resorts currently utilize snowmaking systems to make snow even when there is no natural precipitation. There are many important factors involved in effective snowmaking, however in this question we will simplify the system and assume that a fine mist of spherical water droplets is sprayed into the air and allowed to freeze. Make the following assumptions: water droplets having 0.5 mm diameter are created, 15% of the water evaporates, the temperature of the water droplets is equal from surface to interior (high heat transfer). What is the maximum temperature the water can be maintained at in order for the droplets to remain at 0°C after freezing completely?
 - a. (10) Describe the process, conceptually, that you would follow to solve this problem.

b.	(6) Calculate the temperature.
C	(4) Identify and explain two other factors that would need to be involved in a
0.	(4) Identify and explain two other factors that would need to be involved in a more detailed solution to this problem.

2. This question pertains to the iron-carbon phase diagram, shown below.

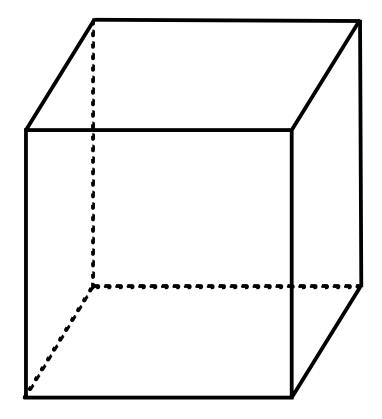


- a. For a sample of 0.25 wt% C steel at 1200°C, what phase or phases will be present, and what will be the composition of each phase, in wt% C? (2)
- b. For a 1 kg sample of 1.25 wt% C steel at 728°C, what will be the mass, in grams, of α ferrite? (2)
- c. For a 1 kg sample of 0.75 wt% C steel at 728°C, what will be the mass, in grams, of α ferrite? (2)
- d. For a 1 kg sample of 4.5 wt% C cast iron at 726°C, what will be the mass, in grams, of carbon that is present as point defects in iron? (2)
- e. For a sample of 3 wt% C cast iron, what will be the minimum temperature to which this sample would need to be heated to ensure no solid remained? (2)

- 3. (10) A footbridge is produced from concrete. The bridge has a rectangular cross-section with height 20 cm and width 100 cm and is designed to cross a span of 3 m. Assume a typical value for the bending strength of concrete of 0.5 MPa, and an acceleration due to gravity of 9.8 N/kg.
 - a. (5) What would be the maximum mass, in kg, that could be supported at the middle of this bridge?

b. (5) Another bridge was built having the same dimensions, however with 5 lengths of steel rebar (reinforcing bar) embedded along the lower surface, aligned with the long axis, of the beam. Assume that the rebar has a 10 mm diameter and a yield strength of 500 MPa, that the entire tensile stress on the lower surface of the beam is supported by the rebar and none by the concrete. What would be the maximum mass, in kg, that could be supported at the middle of this bridge without the rebar experiencing any plastic deformation?

- 4. (10) This question pertains to the crystalline structure of silicon.
 - a. (5) Name the crystal structure of crystalline silicon and in the unit cell below sketch the structure.



b. (5) If the lattice parameter for solid crystalline silicon is 5.4×10^{-10} m, calculate the theoretical density of silicon.

5.	` '	Methane is a widely used fuel for residential heating systems. (2) In the box below write the balanced chemical equation for the combus of 1 mol of gaseous methane(CH4) with 2 mols of gaseous oxygen to for carbon dioxide gas and water vapour.	

b. (2) Determine the standard combustion enthalpy for one mol of gaseous methane.

c. (6) Assuming all of the heat from the combustion of 1 mol of methane goes to heating a 45 m² room with 3 m ceilings, what will the resulting temperature change be to the room? Assume a density of air of 1.225 kg/m³.

6. (5) This question pertains to the band theory of solids. In the boxes below, ske the generalized band structure for conductors, insulators, and intrinsic semiconductors, p-type and n-type semiconductors. On your sketches, label important features, including donor and acceptor levels.									
	Conductor	Insulator	Intrinsic semiconductor						
ţ	p-type semiconductor	n-type semiconductor							

7. Correctly identify each of the following by indicating the matching number in the box beside each description. Numbers may be used more than once. (1 each)							
	 3. 4. 6. 	N-type P-type Point defect Linear imperfection Interfacial defect Volume defect 0.414	8. 0.225 9. 0.732 10. Condu 11. Valend 12. Increa 13. 4 14. 6		15.8 16.12 17.Chain orientation 18.Increasing molecular weight 19.Cross-linking 20.Intrinsic		
		e crystalline imperfection res estic deformation in metals.	sponsible	f. The change that visitength of a metal decreased			
		bon present in iron at comp 0.022 wt% carbon.	ositions	g. The donor level i type semiconductor	s close to this in a n-		
		e coordination number of cat ck salt crystal structure.	tions in	h. The minimum siz fraction of the anior number of 6.	te of a cation as a n size for a coordination		
ро	lym	e strengthening mechanism ers chiefly responsible for clearing beyond necking.		i. Arsenic (As) adde will create this type	ed as a dopant to silicon of semiconductor.		
		e coordination number of ato crystal structure	oms in the		ed as a dopant to silicon of crystalline		

This page intentionally left blank. You may use this page for rough calculations, however, NO work written on this page will be graded.

You may remove these pages from your test.

Constants

1 atm = 101.325 kPa = 1.01325 bar = 14.696 psi
$$N_A = 6.022 \times 10^{23} \text{ mol}^{-1}$$
 $e = 1.602 \times 10^{-19} \text{ C}$

1 eV = 1.602 x 10⁻¹⁹ J
$$\varepsilon_0$$
 = 8.854 × 10⁻¹² $\frac{F}{m}$ R = 8.314 $\frac{J}{mol \cdot K}$ = 0.082067 $\frac{L \cdot atm}{mol \cdot K}$

$$T_{(K)} = T_{(^{\circ}C)} + 273.15$$
 $k = 8.62 \times 10^{-5} \frac{eV}{atom \cdot K}$ $k = 1.38 \times 10^{-23} \frac{J}{atom \cdot K}$ $F = 96486 \text{ C} \cdot \text{mol}^{-1}$

Microstructure

$$LD = {^{\#}}/_{Length} \quad LPF = \frac{length \ of \ atoms}{length \ of \ vector} \quad PD = {^{\#}}/_{Area} \quad PPF = \frac{area \ of \ atoms}{area \ of \ plane} \quad V = \frac{4}{3}\pi r^3$$

$$A = \pi r^2 \quad A_{\Delta} = \frac{1}{2}bh \qquad \rho = \frac{n \cdot A}{V_C \cdot N_A} \qquad \rho = \frac{m}{V} \qquad \rho = \frac{n_A A_A + n_C A_C}{V_C N_A} \qquad APF = \frac{V_S}{V_C}$$

$$N = \frac{N_A \rho}{A}$$
 $N_v = N \exp\left(-\frac{Q_v}{kT}\right)$ $a = 2\sqrt{2}R$ $a = \frac{4}{\sqrt{3}}R$

Mechanical Behaviour

$$\sigma = \frac{F}{A}$$
 $\varepsilon = \frac{\Delta l}{l_o}$ $\sigma = E \varepsilon$ $\sigma_{3-point\ bend} = \frac{3FL}{2w \cdot h^2} x = \frac{-b \pm \sqrt{b^2 - 4ac}}{2a}$

Electrical Behaviour

$$\sigma = n|e|\mu_e + h|e|\mu_h$$
 $\sigma = n|e|\mu_e$ $\sigma = h|e|\mu_h$

Thermodynamics

$$PV = nRT \qquad \Delta U = q + w \qquad \Delta U = q - P_{ext} \Delta V \qquad H \equiv U + PV \quad G \equiv H - TS \qquad \Delta S = \frac{q_{rev}}{T}$$

For process at constant T: $\Delta G = \Delta H - T\Delta S$ $q = mc\Delta T = nC_p\Delta T$ $\Delta G = \Delta H - T\Delta S$

$$W_{phase} = \frac{\textit{length of opposite side of lever}}{\textit{total length of lever}} \qquad \text{For } aA + bB \ \rightarrow cC + dD, \ \ Q = \frac{a_C^c \cdot a_D^d}{a_A^d \cdot a_B^b}$$

 v_i : stoichiometric coefficient Assuming no phase change, constant C_p :

$$\Delta H_{reaction}^{\circ} = (\Sigma v_i \Delta H_{f,i}^{\circ})_{products} - (\Sigma v_i \Delta H_{f,i}^{\circ})_{reactants}$$

$$\Delta S_{reaction}^{\circ} = (\Sigma v_i \Delta S_{m,i}^{\circ})_{products} - (\Sigma v_i \Delta H_{m,i}^{\circ})_{reactants}$$

$$\Delta G_{reaction}^{\circ} = \Delta H_{reaction}^{\circ} - T \Delta S_{reaction}^{\circ} \qquad \qquad \Delta G_{reaction} = \Delta G^{\circ} + RT lnQ$$

$$\Delta G^{\circ} = -RTlnK$$

Electrochemistry

$$E = E^{\circ} - \frac{RT}{nF} lnQ$$
 $E = E^{\circ} - \frac{0.0592}{n} lnQ$, at 25°C $I = \frac{nC}{t}$ $W = nFE^{\circ}$

	0	He 4.0026	10	Ne	20.183	18	Ar	39.948	36	궃	83.80	54	Xe	131.30	98	Rn	(222)				71	r.	174.97	103	Lw	(257)
			10.000		\rightarrow	_				_											\vdash		_			\dashv
		VIIA	6	т с	18.998	17	5	35.453	35	B	79.91	53	_	126.90	82	Aŧ	(210)				70	Yb	173.04	102	Š	(254
		VIA	œ	0 1	15.999	16	S	32.064	34	Se	78.96	25	Те	127.60	84	Ъ	(210)				69	H	168.93	101	Md	(256)
		۸	7	Z ?	14.007	15	۵	30.974	33	As	74.922	51	Sb	121.75	83	Bi	208.98				89	Ē	167.26	100	Fm	(253)
		IVA		0	-		Si	28.086	32	Ge	72.59	20	Sn	118.69	82	Pb	207.19				29	유	164.93	66	Es	(254)
		HIA	2	B	10.811	13	F	26.982	31	Ga	69.72	49	ㅁ	114.82	81	F	204.37				99	Q	162.50	86	Ç	(249)
							:	IIB	30	Zn	65.37	48	Р	112.40	80	Нg	200.59				65	Tp	158.92	6	BK	(247)
	[a]			diate				В	59	Cu	63.54	47	Ag	107.87	79	Au	196.97				64	pg	157.25	96	Cm	(247)
Metal	Nonmetal		:	Intermediate					28	ž	58.71	46	Pd	106.4	78	Ł	195.09				63	En	151.96	98	Am	(243)
							≣{		27	ပိ	58.933	45	Rh	102.91	77	<u>-</u>	192.2				62	Sm	150.35	94	Pn	(242)
	Je				_				56	Pe	55.847	44	Ru	101.07	9/	Os	190.2				61	Pm	(145)	93	Np	(237)
	– Atomic number		Atomic weignt					VIIB	25	M	54.938	43	ည	(66)	75	Re	186.2				09	PN	144.24	92	⊃	238.03
	- Atom	— Symbo	Atom					VIB	24	ప	51.996	42	Mo	95.94	74	>	183.85				59	Ą	140.91	91	Ра	(231)
	Key 29 €	Cu <						VB	23	>	50.942	41	QN	92.91	73	Та	180.95				58	Ce	140.12	06	т	232.04
								INB	22	F	47.90	40	Zr	91.22	72	Ŧ	178.49				57	La	138.91	88	Ac	(227)
							:	E B	21	Sc	44.956	39	>	88.91	Rare	earth	series	Acti-	nide	series		series			series	
		IIA	4	Be	9.0122	12	M	24.312	20	Ca	40.08	38	Sr	87.62	99	Ва	137.34	88	Ra	(226)		Rare earth series			Actinide series	
	I I	H 1.0080	က	.i.	6.939	11	Na	22.990	19	×	39.102	37	Rb	85.47	22	Cs	132.91	87	Ŀ.	(223)		Œ				

Page **14** of **15**

STANDARD FORMATION ENTHALPY, STANDARD ENTROPY AND STANDARD FORMATION GIBBS ENERGY AT 298.15 K

Species	$\Delta_{\mathrm{f}}H^{oldsymbol{o}}$ [kJ/mol]	S° [J/mol·K]	$\Delta_{f} G^{o}$ [kJ/mol]
C (s, graphite)	0	5.74	0
CH ₄ (g)	- 74.81	186.2	-50.75
$C_2H_2(g)$	226.7	200.93	
C₃H ₈ (g)	-103.8	269.9	-23.49
CaC ₂ (s)	-59.8	70.3	
CaF ₂ (s)	-1225	68.87	-1162
CaF ₂ (I)	-1186	92.6	
Ca(OH) ₂ (s)	-987.0	83.0	
CO ₂ (g)	-393.5	213.6	-394.4
Cu ₂ O (s)	-168.6	93.1	
Cu ₂ O (I)	-154.79		
Cu (s)		33.2	
Fe (s)	0	27.3	0
Fe ₂ O ₃ (s)	-824.2	87.4	
H ₂ (g)		130.68	
H ₂ O (g)	-241.8	188.7	-228.6
$H_2O(I)$	-285.8	69	
O ₂ (g)	0	205.0	0

MISCELLANEOUS ENTHALPIES

Substance	Reaction	ΔH [kJ/mol]
F-F	Bond dissociation	157
F	Electron affinity	-328
	$F(g) \rightarrow F^{-}(g)$	
Ca	Second Ionization energy	1734
	Ca (g) \rightarrow Ca ²⁺ (g)	

SPECIFIC HEATS AND HEAT CAPACITIES

OI LOIL TO TILATO AND TILAT OAT ACTITIES								
Substance	Specific Heat c [J/g·K]	Molar Heat Capacity C _p [J/mol·K]						
CO ₂ (g)	0.843	37.1						
Air (g)	1.0							
H ₂ O (g)	2.03	36.4						
$H_2O(I)$	4.184	75.3						
$H_2O(s)$	2.09	37.7						

TEMPERATURES AND ENTHALPIES OF PHASE CHANGES

Substance	Melting Point [°C]	Δ _{fus} Η ^ο [kJ/mol]	Boiling Point [°C]	∆ _{vap} H° [kJ/mol]
Al	658	10.6	2467	284
Ca	851	9.33	1487	162
CH ₄	-182	0.92	-164	8.18
H ₂ O	0	6.01	100	40.7
Fe	1530	14.9	2735	354